

**Amendments to the Claims:**

Please amend claims 1, 3, 5 and 9 as follows.

1. (Currently Amended) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic compound film containing an organic component ~~as a main constituent~~ by using a plasma derived from an etching gas containing an ammonia gas and a fluorine  $F_2$  gas ~~as main constituents~~.

2. (Original) The etching method of claim 1, wherein said etching gas contains an inert gas.

3. (Currently Amended) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component ~~as a main constituent~~ by using a plasma derived from an etching gas containing a hydrogen  $H_2$  gas, a nitrogen  $N_2$  gas, and a fluorine  $F_2$  gas ~~as main constituent, but no  $O_2$  gas~~.

4. (Original) The etching method of claim 3, wherein said etching gas contains an inert gas.

5. (Currently Amended) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component ~~as main constituent~~ by using a plasma derived from an etching gas containing a hydrogen  $H_2$  gas and a nitrogen trifluoride gas ~~as main constituents, but no  $O_2$  gas~~.

6. (Original) The etching method of claim 5, wherein said etching gas contains an inert gas.

7. (Currently Amended) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component ~~as main~~

constituents by using a plasma derived from an etching gas containing a nitrogen N<sub>2</sub> gas and a hydrogen fluoride gas as main constituents.

8. (Original) The etching method of claim 7, wherein said etching gas contains an inert gas.

9. (Original) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a nitrogen H<sub>2</sub> gas and a fluorinated hydrocarbon gas as main constituents, but no O<sub>2</sub> gas.

10. (Original) The etching method of claim 9, wherein said etching gas contains an inert gas.

11. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon dioxide gas and a fluorine gas as main constituents.

12. (Withdrawn) The etching method of claim 11, wherein said etching gas contains an inert gas.

13. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon dioxide gas and a fluorinated hydrocarbon gas as main constituents.

14. (Withdrawn) The etching method of claim 13, wherein said etching gas contains an inert gas.

15. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon monoxide gas and a fluorinated gas as main constituents.

16. (Withdrawn) The etching method of claim 15, wherein said etching gas contains an inert gas.

17. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon monoxide gas and a fluorinated gas as main constituents.

18. (Withdrawn) The etching method of claim 17, wherein said etching gas contains an inert gas.